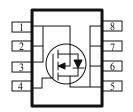
## N-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

| PRODUCT SUMMARY |                                 |     |  |  |  |
|-----------------|---------------------------------|-----|--|--|--|
| $V_{DS}(V)$     | $r_{DS(on)} m(\Omega)$ $I_D(A)$ |     |  |  |  |
| 20              | $22@V_{CS}=4.5V$                | 9.7 |  |  |  |
|                 | $28@V_{CS}=2.5V$                | 8.6 |  |  |  |

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED) |  |                  |            |       |  |  |
|--|--|------------------|------------|-------|--|--|
| Parameter Parameter  |  | Symbol           | Limit      | Units |  |  |
| Drain-Source Voltage   |  |                  | 20         | V     |  |  |
| Gate-Source Voltage  |  |                  | ±8         | v     |  |  |
| C t D · C a  | T <sub>A</sub> =25°C                       |                  | ±9.7       |       |  |  |
| Continuous Drain Current <sup>a</sup>                            | $T_A=25^{\circ}C$ $T_A=70^{\circ}C$        | 1D               | ±8.0       | Α     |  |  |
| Pulsed Drain Current <sup>b</sup>                                |  |                  | ±50        |       |  |  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>        |  |                  | 2.3        | Α     |  |  |
| D D a  | T <sub>A</sub> =25°C                       | D                | 3.1        | W     |  |  |
| Power Dissipation <sup>a</sup>                                   | $T_{A}=25^{\circ}C$<br>$T_{A}=70^{\circ}C$ | FD               | 2.2        |       |  |  |
| Operating Junction and Storage Temperature Range                 |  | $T_{J}, T_{stg}$ | -55 to 150 | °C    |  |  |

| THERMAL RESISTANCE RATINGS               |              |                |       |      |  |
|--|--------------|----------------|-------|------|--|
| Parameter                                | Symbol       | Maximum        | Units |      |  |
| M · T · · · · · · · · · · · · · · · · ·  | t <= 10 sec  | .D             | 50    | °C/W |  |
| Maximum Junction-to-Ambient <sup>a</sup> | Steady State | $R_{	heta JA}$ | 92    | °C/W |  |

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

| SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED) |                            |   |        |     |      |      |  |
|---|----------------------------|---|--------|-----|------|------|--|
| Parameter   | Counch of                  | Total Conditions  | Limits |     |      | Unit |  |
| rarameter   | Symbol Test Conditions     |   | Min    | Тур | Max  | Unit |  |
| Static  |                            |   |        |     |      |      |  |
| Drain-Source Breakdown Voltage                                | $V_{(BR)DSS}$              | $V_{GS} = 0 \text{ V}, I_D = 250 \text{ uA}$                                | 20     |     |      | V    |  |
| Gate-Threshold Voltage  | $V_{GS(th)}$               | $V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$                                   | 1.0    |     |      | ľ    |  |
| Gate-Body Leakage   | $I_{GSS}$                  | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$                            |        |     | ±100 | nA   |  |
| Zoro Coto Voltogo Droin Current                               |                            | $V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$                               | 1      |     | 1    | 4    |  |
| Zero Gate Voltage Drain Current                               | $I_{DSS}$                  | $V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$   |        |     | 25   | uA   |  |
| On-State Drain Current <sup>A</sup>                           | $I_{D(on)}$                | $V_{DS} = 5 \text{ V}, V_{GS} = \pm 12 \text{ V}$                           | 20     |     |      | A    |  |
| Dunin Grand On Braintan A                                     | r <sub>DS(on)</sub>        | $V_{GS} = 4.5 \text{ V}, I_D = 9.7 \text{ A}$                               |        |     | 22   | -m0  |  |
| Drain-Source On-Resistance <sup>A</sup>                       |                            | $V_{GS} = 2.5 \text{ V}, I_D = 8.6 \text{ A}$                               |        |     | 28   | mΩ   |  |
| Forward Tranconductance <sup>A</sup>                          | $\mathbf{g}_{\mathrm{fs}}$ | $V_{DS} = 15 \text{ V}, I_{D} = 9.7 \text{ A}$                              |        | 40  |      | S    |  |
| Diode Forward Voltage   | $V_{\mathrm{SD}}$          | $I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$                                 |        | 0.7 |      | V    |  |
| Dynamic <sup>b</sup>  |                            |   |        |     |      |      |  |
| Total Gate Charge   | $Q_{g}$                    | V = 15 V V = 45 V   |        | 5.5 |      |      |  |
| Gate-Source Charge  | $Q_{gs}$                   | $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$<br>$I_{D} = 9.7 \text{ A}$ |        | 1.0 |      | nC   |  |
| Gate-Drain Charge   | $Q_{gd}$                   | $I_{\rm D} = 9.7$ A   |        | 1.4 |      | 1    |  |
| Turn-On Delay Time  | $t_{d(on)}$                |   |        | 20  |      |      |  |
| Rise Time   | t <sub>r</sub>             | $V_{DD} = 25 \text{ V}, R_L = 25 \Omega, I_D = 1 \text{ A},$                |        | 9   |      | nS   |  |
| Turn-Off Delay Time   | $t_{d(off)}$               | $V_{GEN} = 10 \text{ V}$  |        | 70  |      | ns   |  |
| Fall-Time   | $t_{ m f}$                 |   |        | 20  |      | 1    |  |

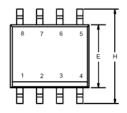
## Notes

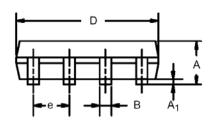
- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Package Information

SO-8: 8LEAD





|                | MILLIN   | IETERS | INC       | IES   |  |
|----------------|----------|--------|-----------|-------|--|
| Dim            | Min      | Max    | Min       | Max   |  |
| Α              | 1.35     | 1.75   | 0.053     | 0.069 |  |
| A <sub>1</sub> | 0.10     | 0.20   | 0.004     | 0.008 |  |
| В              | 0.35     | 0.51   | 0.014     | 0.020 |  |
| С              | 0.19     | 0.25   | 0.0075    | 0.010 |  |
| D              | 4.80     | 5.00   | 0.189     | 0.196 |  |
| E              | 3.80     | 4.00   | 0.150     | 0.157 |  |
| е              | 1.27 BSC |        | 0.050 BSC |       |  |
| Н              | 5.80     | 6.20   | 0.228     | 0.244 |  |
| h              | 0.25     | 0.50   | 0.010     | 0.020 |  |
| L              | 0.50     | 0.93   | 0.020     | 0.037 |  |
| q              | 0°       | 8°     | 0°        | 8°    |  |

